

/ Descriptions

Ultrafast Recovery Diode in a TO-220AC Plastic Package.

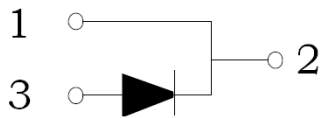
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

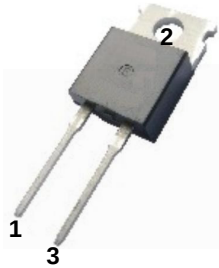
/ Applications

For high frequency, high voltage, high current rectifier diode, freewheeling diode.

/ Equivalent Circuit



/ Pinning



PIN1 2 Cathode

PIN 3 Anode

/ h_{FE} Classifications & Marking

See Marking Instructions

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Average Forward Current	I_F	1 × 20	A
Peak forward surge current	I_{FSM}	250	A
Typical Thermal Resistance Junction to Case	$R_{\theta Jc}$	2.8	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

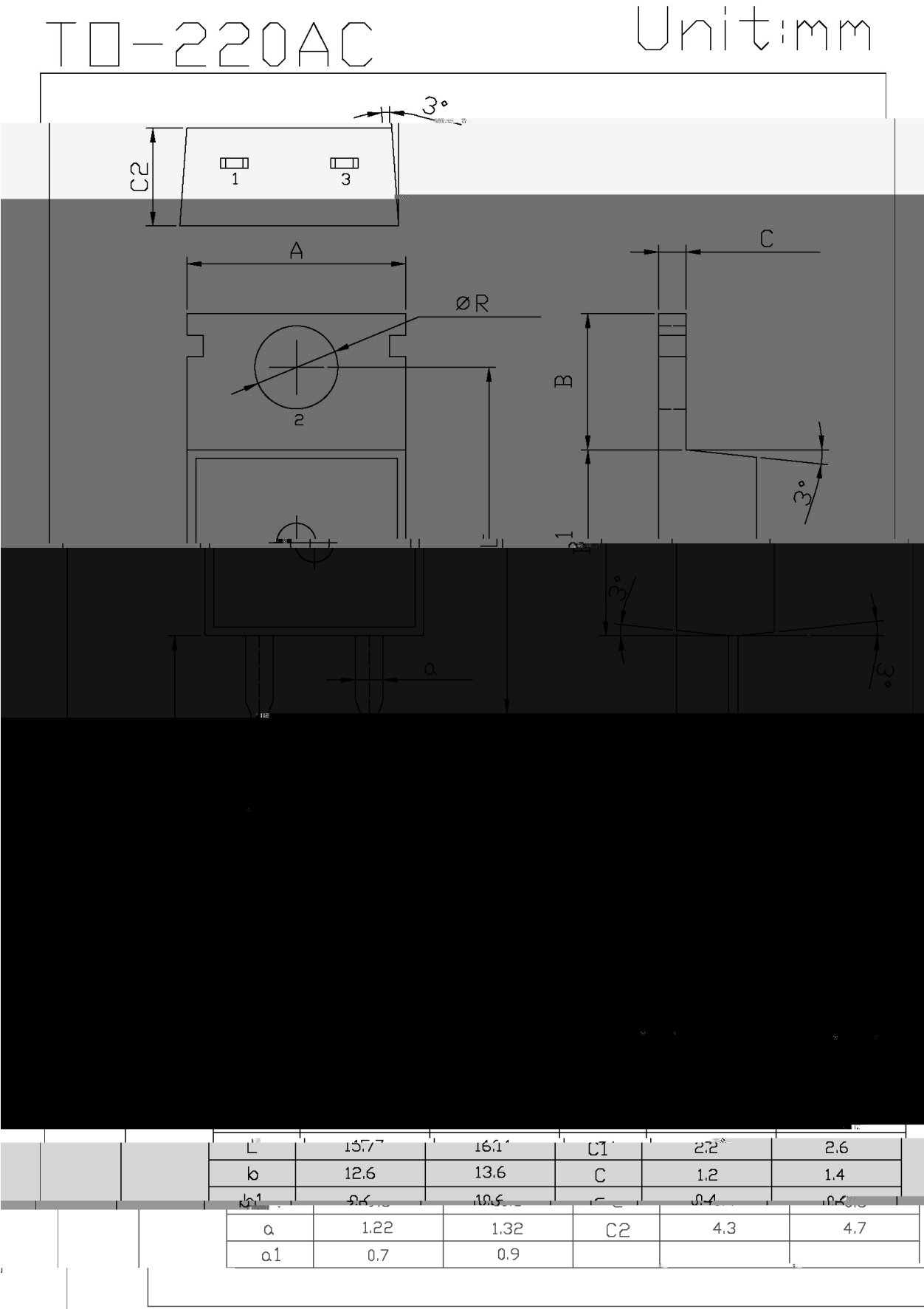
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=5.0A$ $T_C=25$			1.35	V
		$I_F=5.0A$ $T_C=150$			1.15	
		$I_F=20A$ $T_C=25$			1.65	
		$I_F=20A$ $T_C=150$			1.25	
Instantaneous Reverse Current(Note1)	I_R	$V_R=600V$ $T_a=25$			0.25	mA
		$V_R=420V$ $T_a=150$			1.0	
		$V_R=600V$ $T_a=150$			2.0	
Reverse Recovery Time	t_{rr}	$I_F=0.5A$ $I_R=1.0A$ $I_{RR}=0.25A$			50	ns

Notes

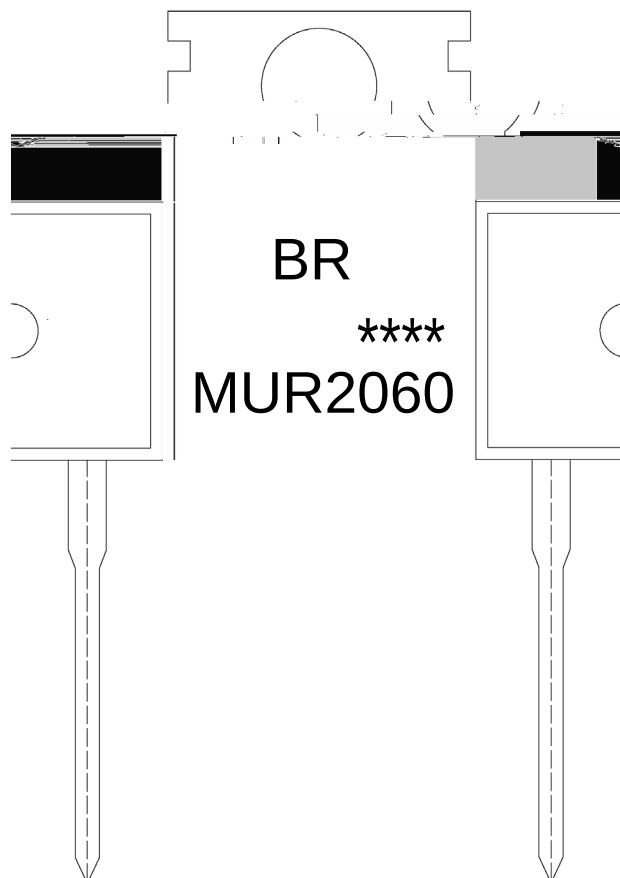
- Short duration pulse test used to minimize self-heating effect.
- Unless otherwise noted, values for the parameters of a single chip

MUR2060

/ Package Dimensions



/ Marking Instructions



Note:

BR:

Company Code

MUR2060

Product Type.

****:

Lot No. Code, code change with Lot No.

300

100

0

1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255	5	5	0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ BULK

[illegible]